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Eğitim Bilgileri

Doktora, Sivas Cumhuriyet Üniversitesi, Fen Fakültesi, Fizik Bölümü, Türkiye 1995 - 2000

Yüksek Lisans, Sivas Cumhuriyet Üniversitesi, Fen Fakültesi, Fizik Bölümü, Türkiye 1992 - 1994

Lisans, Sivas Cumhuriyet Üniversitesi, Fen Fakültesi, Fizik Bölümü, Türkiye 1985 - 1989

Yaptığı Tezler

Doktora, DELTA-KATKILI GaAs YAPILARDA ELEKTRONİK YAPI, Sivas Cumhuriyet Üniversitesi, Fen Fakültesi, Fizik Bölümü, 2000

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